

## Graphene growth directly on functional substrate

C. S. Lee, L. Baraton, Z. B. He, Jean-Luc Maurice, D. Pribat, C. S. Cojocaru

► **To cite this version:**

C. S. Lee, L. Baraton, Z. B. He, Jean-Luc Maurice, D. Pribat, et al.. Graphene growth directly on functional substrate. 2010. hal-00525357

**HAL Id: hal-00525357**

**<https://hal-polytechnique.archives-ouvertes.fr/hal-00525357>**

Submitted on 11 Oct 2010

**HAL** is a multi-disciplinary open access archive for the deposit and dissemination of scientific research documents, whether they are published or not. The documents may come from teaching and research institutions in France or abroad, or from public or private research centers.

L'archive ouverte pluridisciplinaire **HAL**, est destinée au dépôt et à la diffusion de documents scientifiques de niveau recherche, publiés ou non, émanant des établissements d'enseignement et de recherche français ou étrangers, des laboratoires publics ou privés.

Graphene growth directly on functional substrate

C. S. Lee a,, L. Baraton a, Z. He a, J,-L. Maurice a, D. Pribat a,b, C. S. Cojocaru a

a Laboratoire de Physique des Interfaces et Couches Minces(LPICM), CNRS, UMR 7647,  
Ecole Polytechnique, Route de Saclay, 91128, Palaiseau Cedex, France

b Department of Energy Science, Sungkyunkwan University, Suwon 440-746, Korea

Corresponding author. Tel.: +33 1 6933 4359

E-mail address: changseok.lee@polytechnique.edu (C. S. Lee).

Figures

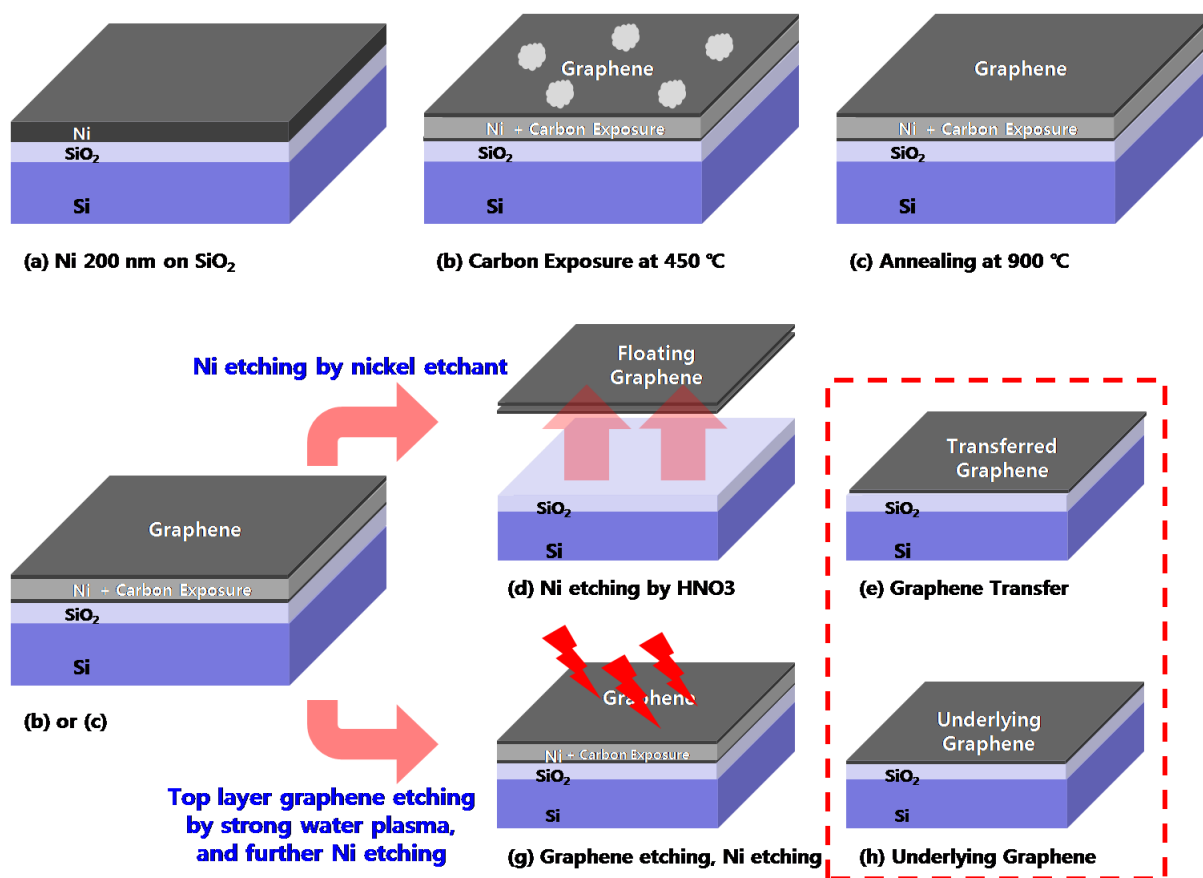


Figure 1. General process for plasma-assisted graphene growth

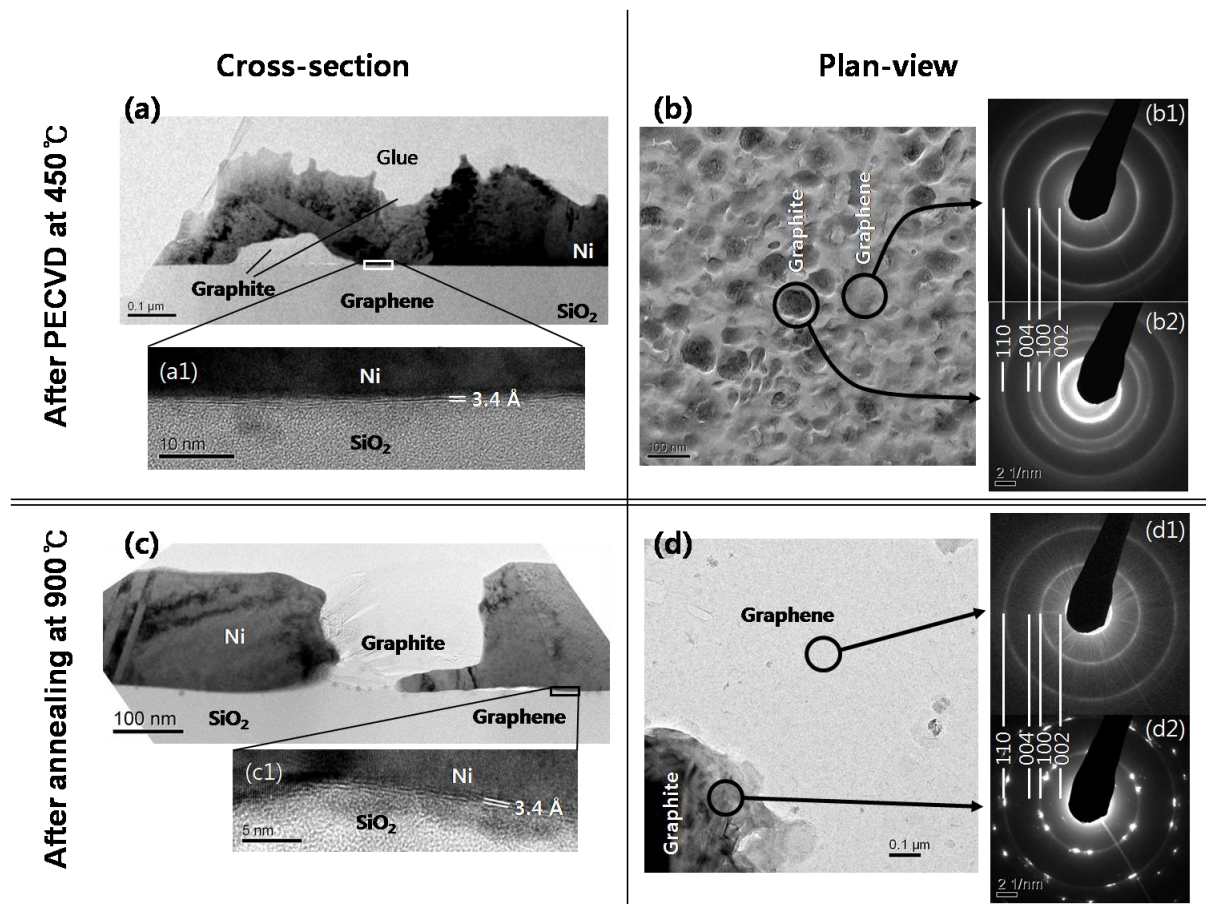


Figure 2. TEM images of the samples after growth by PE-CVD at 450°C for 12 min (a,b), and after an additional annealing treatment in vacuum at 900°C for 18 min (c,d). (a, c) cross-sections where graphite blocks can be seen, together with interfacial graphene in the two cases. The latter (a1, c1) appears continuous over several tens of nm, and more so before annealing. (b, d) plan-views obtained after Ni etching, and depositing the remaining layer on a TEM holey-carbon grid. Images recorded in holey regions (no contribution of amorphous carbon). The diffraction patterns (b1 and d1) indicate that the background consists of nanocrystalline graphene, with random orientation of the nano-grains in the plane (see fig. 3). Note the absence of 002 and 004 reflections indicating a good alignment of the graphene layers in the plane. The graphite blocks are small pillars or onions, with (002) planes parallel to the beam before annealing (b2), while they are flat with no (002) planes visible after annealing (d2).

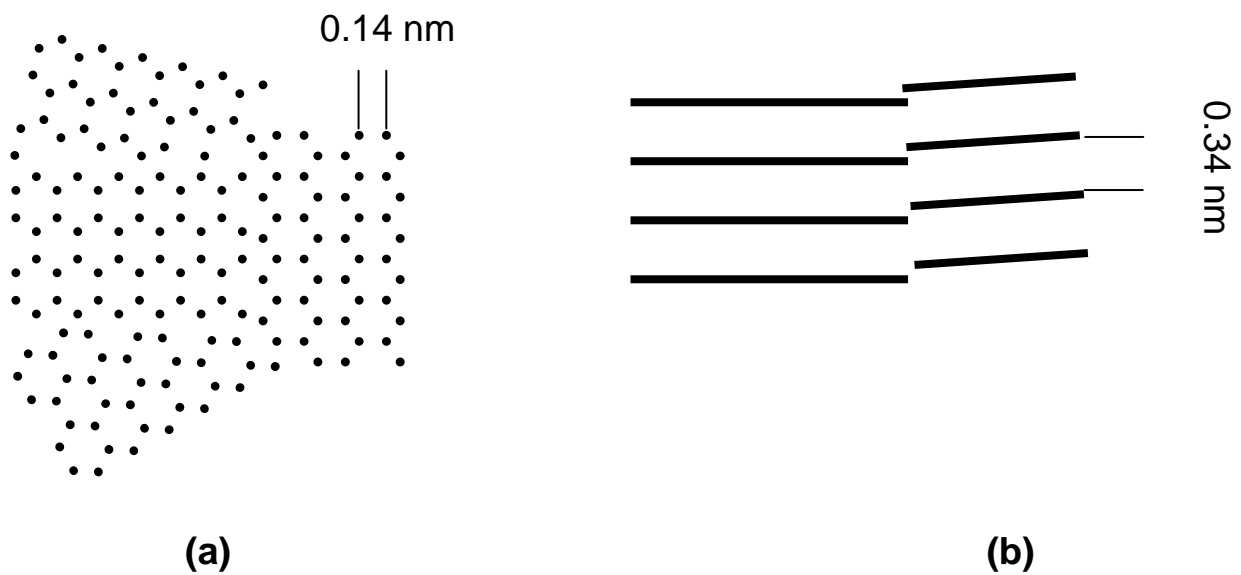


Figure 3. Schematic of the graphene structure in the plane (a) and perpendicular to the plane (b). Atomic positions in (a) are given for visualising the in-plane misorientation of four nm-sized grains; they do not represent, of course, actual positions.

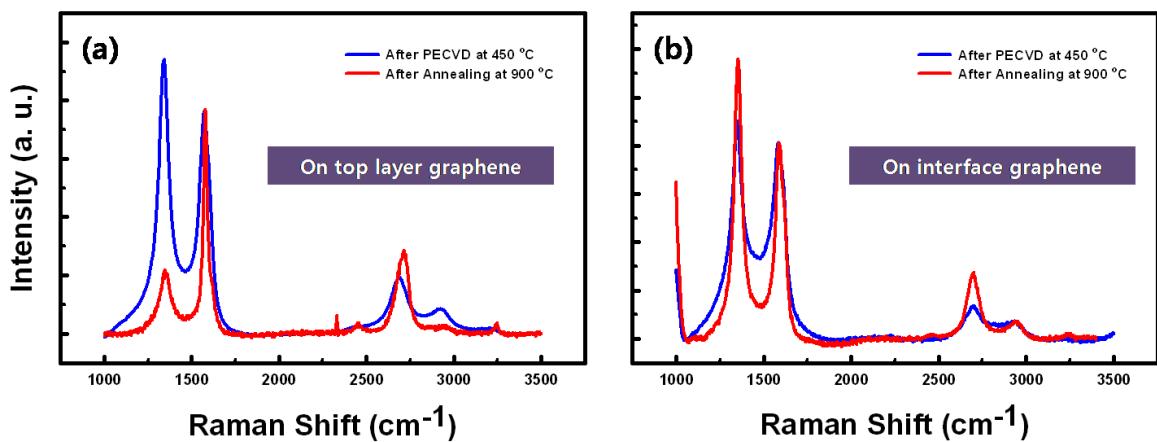


Figure 4. The change of raman spectra after PECVD(blue color) and after Annaling(red color) on (a) top layer graphene, (b) interface graphene, respectively..jpg

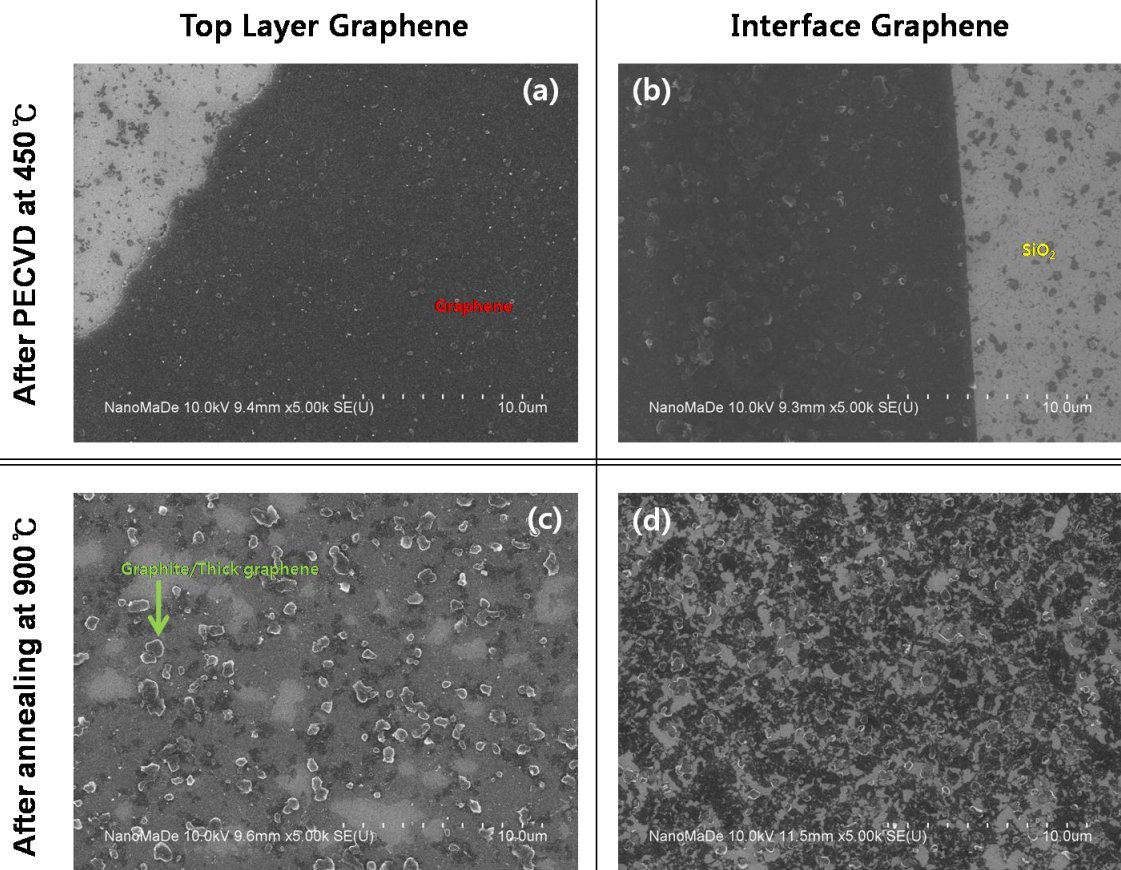


Figure 5. SEM images